UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/578,369	05/05/2006	Syo-ichi Takamizawa	127101	8987
25944 7590 03/25/2008 OLIFF & BERRIDGE, PLC			EXAMINER	
P.O. BOX 3208	50	KUNEMUND, ROBERT M		
ALEXANDRIA, VA 22320-4850			ART UNIT	PAPER NUMBER
			1792	
			MAIL DATE	DELIVERY MODE
			03/25/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
Office Action Comments	10/578,369	TAKAMIZAWA ET AL.				
Office Action Summary	Examiner	Art Unit				
	Robert M. Kunemund	1792				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on						
	-· action is non-final.					
<i>;</i> —	/ 					
closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
ologod in addordance with the practice and c	x parte gaayle, 1000 G.B. 11, 10	0.0.210.				
Disposition of Claims						
4)⊠ Claim(s) <u>10-34</u> is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>10-34</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or						
Application Papers						
9) The specification is objected to by the Examiner. 10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.03(a).						
11) The oath or declaration is objected to by the Exa		, ,				
The dainer decidation is objected to by the Ext	armier. Note the attached emec	7,00,011,011,011,011,01				
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 5/06.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal Pa	(PTO-413) ate				

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 10, 11, 14, and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wise (Jp 09-120947) in view of Satoshi (Jp 10-906955).

The Wise reference teaches an epitaxial method note entire reference. A substrate of silicon is first treated in a hydrofluoric acid bath to remove oxide films from the main surface, note translation, page 2. Then the substrate is placed into an epitaxial growth chamber. In the chamber, the substrate is baked in a hydrogen atmosphere in order to remove the oxide from the surface. This is done around 900 c. After baking a first thin layer of silicon is deposited, and then the main layer of silicon is

grown on the first layer. The second layer growth is done at temperatures higher then the first layer, note page 3. The first layer is doped by the diffusion of dopants from the substrate. The sole difference between the instant claims and the prior art is the back side oxide film. However, the Satoshi reference teaches creating a silicon dioxide film on the back side of silicon substrates used in epitaxial growth, note page 1 of translation. It would have been obvious to one of ordinary skill in the art to modify the Wise reference by the teachings of the Satoshi reference to cover the back side of the silicon wafer in order to prevent auto doping from the back side.

Claims 12, 13, 15 to 19, 21 to 34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wise (Jp 09-120947) in view of Satoshi (Jp 10-906955).

The Wise and Satoshi references are relied on for the same reasons as stated, supra, and differ from the instant claims in the thicknesses of the layers, time between steps, and dopant amounts. However, in the absence of unexpected results, it would have been obvious to one of ordinary skill in the art to determine through routine experimentation the optimum, operable layer thickness, time between steps and dopant amounts in the Wise process in order to create the desired properties in the layers for future use in device manufacture and time for the substrate to adjust to differing conditions.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Robert M. Kunemund whose telephone number is 571-272-1464. The examiner can normally be reached on 8 hours.

Application/Control Number: 10/578,369 Page 4

Art Unit: 1792

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Barr can be reached on 571-272-1414. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Robert M Kunemund Primary Examiner Art Unit 1792

RMK /Robert M Kunemund/ Primary Examiner, Art Unit 1792